

Ming Liu

List of Publications by Year in Descending Order

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Version: 2024-04-20

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

215
papers

11,459
citations

57
h-index

99
g-index

228
ext. papers

13,523
ext. citations

6.7
avg, IF

6.32
L-index

#	Paper	IF	Citations
215	Programme of self-reactive innate-like T cell-mediated cancer immunity.. <i>Nature</i> , 2022 ,	50.4	3
214	Memristive technologies for data storage, computation, encryption, and radio-frequency communication. <i>Science</i> , 2022 , 376,	33.3	24
213	Hybrid memristor-CMOS neurons for in-situ learning in fully hardware memristive spiking neural networks. <i>Science Bulletin</i> , 2021 , 66, 1624-1624	10.6	13
212	Fascin inhibitor increases intratumoral dendritic cell activation and anti-cancer immunity. <i>Cell Reports</i> , 2021 , 35, 108948	10.6	6
211	Resistive switching memory for high density storage and computing*. <i>Chinese Physics B</i> , 2021 , 30, 058702.2	7.2	3
210	Single-cell sequencing links multiregional immune landscapes and tissue-resident T cells in ccRCC to tumor topology and therapy efficacy. <i>Cancer Cell</i> , 2021 , 39, 662-677.e6	24.3	28
209	Evolution of the conductive filament system in HfO-based memristors observed by direct atomic-scale imaging.. <i>Nature Communications</i> , 2021 , 12, 7232	17.4	13
208	Two-dimensional materials for next-generation computing technologies. <i>Nature Nanotechnology</i> , 2020 , 15, 545-557	28.7	196
207	Metal-Semiconductor-Metal Ga ₂ O ₃ Solar-Blind Photodetectors with a Record-High Responsivity Rejection Ratio and Their Gain Mechanism. <i>ACS Photonics</i> , 2020 , 7, 812-820	6.3	69
206	An artificial spiking afferent nerve based on Mott memristors for neurorobotics. <i>Nature Communications</i> , 2020 , 11, 51	17.4	105
205	Modulating the filament rupture degree of threshold switching device for self-selective and low-current nonvolatile memory application. <i>Nanotechnology</i> , 2020 , 31, 144002	3.4	2
204	Oxide-Based Electrolyte-Gated Transistors for Spatiotemporal Information Processing. <i>Advanced Materials</i> , 2020 , 32, e2003018	24	48
203	TGF- β suppresses type 2 immunity to cancer. <i>Nature</i> , 2020 , 587, 115-120	50.4	63
202	Cancer immunotherapy via targeted TGF- β signalling blockade in T cells. <i>Nature</i> , 2020 , 587, 121-125	50.4	76
201	A Highlight of the Mechanisms of Immune Checkpoint Blocker Resistance. <i>Frontiers in Cell and Developmental Biology</i> , 2020 , 8, 580140	5.7	7
200	High-Contrast Polymorphic Luminogen Formed through Effect of Tiny Differences in Intermolecular Interactions on the Intramolecular Charge Transfer Process. <i>Advanced Optical Materials</i> , 2020 , 8, 2000436	8.1	8
199	Ultrahigh-Performance Solar-Blind Photodetector Based on α -Phase-Dominated Ga ₂ O ₃ Film With Record Low Dark Current of 81 fA. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1483-1486	4.4	36

198	Room Temperature-Processed α -IGZO Schottky Diode for Rectifying Circuit and Bipolar 1D1R Crossbar Applications. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 4087-4091	2.9	12
197	Amorphous Gallium Oxide-Based Gate-Tunable High-Performance Thin Film Phototransistor for Solar-Blind Imaging. <i>Advanced Electronic Materials</i> , 2019 , 5, 1900389	6.4	50
196	. <i>IEEE Electron Device Letters</i> , 2019 , 40, 718-721	4.4	14
195	Review of deep ultraviolet photodetector based on gallium oxide. <i>Chinese Physics B</i> , 2019 , 28, 018501	1.2	42
194	Optimization of Electrical Properties of MoS ₂ Field-Effect Transistors by Dipole Layer Coulombic Interaction With Trap States. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019 , 13, 1900007	2.5	4
193	Thermoelectric Seebeck Effect of Disordered Organic Semiconductors 2019 , 79-111		
192	Enhancement-Mode β -Ga ₂ O ₃ Metal Oxide Semiconductor Field-Effect Solar-Blind Phototransistor With Ultrahigh Detectivity and Photo-to-Dark Current Ratio. <i>IEEE Electron Device Letters</i> , 2019 , 40, 742-745	4.4	40
191	Suppression of Filament Overgrowth in Conductive Bridge Random Access Memory by TaO/TaO Bi-Layer Structure. <i>Nanoscale Research Letters</i> , 2019 , 14, 111	5	10
190	High-Performance Metal-Organic Chemical Vapor Deposition Grown ϵ -Ga ₂ O ₃ Solar-Blind Photodetector With Asymmetric Schottky Electrodes. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1475-1478	4.4	59
189	Manipulating Polymer Donors Toward a High-Performance Polymer Acceptor Based On a Fused Perylene diimide Building Block With a Built-In Twisting Configuration. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 29765-29772	9.5	10
188	Observing large ferroelectric polarization in top-electrode-free Al:HfO ₂ thin films with Al-rich strip structures. <i>Applied Physics Letters</i> , 2019 , 115, 152901	3.4	3
187	Improvement of Endurance in HZO-Based Ferroelectric Capacitor Using Ru Electrode. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1744-1747	4.4	41
186	Resistive Switching Devices: Mechanism, Performance and Integration 2019 , 843-911		
185	Fusion or non-fusion of quasi-two-dimensional fused perylene diimide acceptors: the importance of molecular geometry for fullerene-free organic solar cells. <i>Journal of Materials Chemistry A</i> , 2019 , 7, 27493-27502	13.3	14
184	A Dual-Functional IGZO-Based Device With Schottky Diode Rectifying and Resistance Switching Behaviors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 24-27	4.4	15
183	Transcriptomic Profiling of the Tumor Microenvironment Reveals Distinct Subgroups of Clear Cell Renal Cell Cancer: Data from a Randomized Phase III Trial. <i>Cancer Discovery</i> , 2019 , 9, 510-525	24.4	88
182	Performance-Enhancing Selector via Symmetrical Multilayer Design. <i>Advanced Functional Materials</i> , 2019 , 29, 1808376	15.6	38
181	Understanding the transport mechanism of organic-inorganic perovskite solar cells: The effect of exciton or free-charge on diffusion length. <i>Organic Electronics</i> , 2019 , 66, 163-168	3.5	9

180	Recommended Methods to Study Resistive Switching Devices. <i>Advanced Electronic Materials</i> , 2019 , 5, 1800143	6.4	297
179	Investigation of Retention Behavior of TiOx/Al2O3 Resistive Memory and Its Failure Mechanism Based on Meyer-Neldel Rule. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 957-962	2.9	8
178	Full imitation of synaptic metaplasticity based on memristor devices. <i>Nanoscale</i> , 2018 , 10, 5875-5881	7.7	75
177	Cancer Cell Membrane-Biomimetic Nanoprobes with Two-Photon Excitation and Near-Infrared Emission for Intravital Tumor Fluorescence Imaging. <i>ACS Nano</i> , 2018 , 12, 1350-1358	16.7	71
176	Breaking the Current-Retention Dilemma in Cation-Based Resistive Switching Devices Utilizing Graphene with Controlled Defects. <i>Advanced Materials</i> , 2018 , 30, e1705193	24	157
175	Characterization of the inhomogeneous barrier distribution in a Pt/(100)EGa2O3 Schottky diode via its temperature-dependent electrical properties. <i>AIP Advances</i> , 2018 , 8, 015316	1.5	39
174	Design of CMOS Compatible, High-Speed, Highly-Stable Complementary Switching with Multilevel Operation in 3D Vertically Stacked Novel HfO2/Al2O3/TiOx (HAT) RRAM. <i>Advanced Electronic Materials</i> , 2018 , 4, 1700561	6.4	45
173	Origin of negative resistance in anion migration controlled resistive memory. <i>Applied Physics Letters</i> , 2018 , 112, 133108	3.4	5
172	Improvement of durability and switching speed by incorporating nanocrystals in the HfOx based resistive random access memory devices. <i>Applied Physics Letters</i> , 2018 , 113, 023105	3.4	44
171	A review for polaron dependent charge transport in organic semiconductor. <i>Organic Electronics</i> , 2018 , 61, 223-234	3.5	26
170	Modulating 3D memristor synapse by analog spiking pulses for bioinspired neuromorphic computing. <i>Science China: Physics, Mechanics and Astronomy</i> , 2018 , 61, 1	3.6	9
169	Proton Radiation Effects on Y-Doped HfO2-Based Ferroelectric Memory. <i>IEEE Electron Device Letters</i> , 2018 , 39, 823-826	4.4	14
168	Effects of Capping Electrode on Ferroelectric Properties of Hf0.5Zr0.5O2 Thin Films. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1207-1210	4.4	70
167	Negative differential resistance effect induced by metal ion implantation in SiO film for multilevel RRAM application. <i>Nanotechnology</i> , 2018 , 29, 054001	3.4	11
166	Novel perylene diimide-based polymers with electron-deficient segments as the comonomer for efficient all-polymer solar cells. <i>Journal of Materials Chemistry A</i> , 2018 , 6, 414-422	13	54
165	Simultaneous near-infrared and green fluorescence from single conjugated polymer dots with aggregation-induced emission fluorogen for cell imaging. <i>Journal of Materials Chemistry B</i> , 2018 , 6, 7871-7876	7.3	7
164	A Review for Compact Model of Thin-Film Transistors (TFTs). <i>Micromachines</i> , 2018 , 9,	3.3	22
163	Design, Construction, and Testing of a Gasifier-Specific Solid Oxide Fuel Cell System. <i>Energies</i> , 2018 , 11, 1985	3.1	7

162	Photoelectric Plasticity in Oxide Thin Film Transistors with Tunable Synaptic Functions. <i>Advanced Electronic Materials</i> , 2018 , 4, 1800556	6.4	56
161	Bipolar Analog Memristors as Artificial Synapses for Neuromorphic Computing. <i>Materials</i> , 2018 , 11,	3.5	32
160	Recent updates on cancer immunotherapy. <i>Precision Clinical Medicine</i> , 2018 , 1, 65-74	6.7	66
159	TGF- β Control of Adaptive Immune Tolerance: A Break From Treg Cells. <i>BioEssays</i> , 2018 , 40, e1800063	4.1	33
158	A Compact Model for Drift and Diffusion Memristor Applied in Neuron Circuits Design. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 4290-4296	2.9	14
157	HfO ₂ -Based Highly Stable Radiation-Immune Ferroelectric Memory. <i>IEEE Electron Device Letters</i> , 2017 , 38, 330-333	4.4	25
156	Confining Cation Injection to Enhance CBRAM Performance by Nanopore Graphene Layer. <i>Small</i> , 2017 , 13, 1603948	11	113
155	Resistive Switching Performance Improvement via Modulating Nanoscale Conductive Filament, Involving the Application of Two-Dimensional Layered Materials. <i>Small</i> , 2017 , 13, 1604306	11	105
154	Carrier thermoelectric transport model for black phosphorus field-effect transistors. <i>Chemical Physics Letters</i> , 2017 , 678, 271-274	2.5	2
153	Crystal that remembers: several ways to utilize nanocrystals in resistive switching memory. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 303002	3	31
152	A cell-based clustering model for the reset statistics in RRAM. <i>Applied Physics Letters</i> , 2017 , 110, 123503	3.4	5
151	Fused Perylene Diimide-Based Polymeric Acceptors for Efficient All-Polymer Solar Cells. <i>Macromolecules</i> , 2017 , 50, 7559-7566	5.5	57
150	Temperature, electric-field, and carrier-density dependence of hopping magnetoresistivity in disordered organic semiconductors. <i>Physical Review B</i> , 2017 , 96,	3.3	4
149	Complementary Switching in 3D Resistive Memory Array. <i>Advanced Electronic Materials</i> , 2017 , 3, 1700287	4.4	28
148	Light-Gated Memristor with Integrated Logic and Memory Functions. <i>ACS Nano</i> , 2017 , 11, 11298-11305	16.7	116
147	Variability Improvement of TiO ₂ /AlO _x Bilayer Nonvolatile Resistive Switching Devices by Interfacial Band Engineering with an Ultrathin AlO Dielectric Material. <i>ACS Omega</i> , 2017 , 2, 6888-6895	3.9	34
146	Foxp3-independent mechanism by which TGF- β controls peripheral T cell tolerance. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2017 , 114, E7536-E7544	11.5	27
145	Electronic imitation of behavioral and psychological synaptic activities using TiO ₂ /AlO _x -based memristor devices. <i>Nanoscale</i> , 2017 , 9, 14442-14450	7.7	76

144	Investigation on the Conductive Filament Growth Dynamics in Resistive Switching Memory via a Universal Monte Carlo Simulator. <i>Scientific Reports</i> , 2017 , 7, 11204	4.9	14
143	Intrinsic anionic rearrangement by extrinsic control: transition of RS and CRS in thermally elevated TiN/HfO/Pt RRAM. <i>Nanoscale</i> , 2017 , 9, 18908-18917	7.7	30
142	Highly fluorescent hyperbranched BODIPY-based conjugated polymer dots for cellular imaging. <i>Chemical Communications</i> , 2017 , 53, 8612-8615	5.8	21
141	Quinoxaline-based conjugated polymers for polymer solar cells. <i>Polymer Chemistry</i> , 2017 , 8, 4613-4636	4.9	62
140	Emulating Short-Term and Long-Term Plasticity of Bio-Synapse Based on Cu/a-Si/Pt Memristor. <i>IEEE Electron Device Letters</i> , 2017 , 38, 1208-1211	4.4	89
139	Resistive random access memory (RRAM) technology: From material, device, selector, 3D integration to bottom-up fabrication. <i>Journal of Electroceramics</i> , 2017 , 39, 21-38	1.5	57
138	Fatigue mechanism of yttrium-doped hafnium oxide ferroelectric thin films fabricated by pulsed laser deposition. <i>Physical Chemistry Chemical Physics</i> , 2017 , 19, 3486-3497	3.6	56
137	Recent Development on Narrow Bandgap Conjugated Polymers for Polymer Solar Cells. <i>Polymers</i> , 2017 , 9,	4.5	32
136	Super non-linear RRAM with ultra-low power for 3D vertical nano-crossbar arrays. <i>Nanoscale</i> , 2016 , 8, 15629-36	7.7	72
135	Tumor immune microenvironment characterization in clear cell renal cell carcinoma identifies prognostic and immunotherapeutically relevant messenger RNA signatures. <i>Genome Biology</i> , 2016 , 17, 231	18.3	391
134	Highly improved resistive switching performances of the self-doped Pt/HfO ₂ :Cu/Cu devices by atomic layer deposition. <i>Science China: Physics, Mechanics and Astronomy</i> , 2016 , 59, 1	3.6	12
133	Eliminating Negative-SET Behavior by Suppressing Nanofilament Overgrowth in Cation-Based Memory. <i>Advanced Materials</i> , 2016 , 28, 10623-10629	24	161
132	A review of carrier thermoelectric-transport theory in organic semiconductors. <i>Physical Chemistry Chemical Physics</i> , 2016 , 18, 19503-25	3.6	71
131	Physical model of Seebeck coefficient under surface dipole effect in organic thin-film transistors. <i>Organic Electronics</i> , 2016 , 29, 27-32	3.5	16
130	Analysis on the Filament Structure Evolution in Reset Transition of Cu/HfO ₂ /Pt RRAM Device. <i>Nanoscale Research Letters</i> , 2016 , 11, 269	5	8
129	Highly scalable resistive switching memory in metal nanowire crossbar arrays fabricated by electron beam lithography. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 02G105	1.3	8
128	Occurrence of Resistive Switching and Threshold Switching in Atomic Layer Deposited Ultrathin (2 nm) Aluminium Oxide Crossbar Resistive Random Access Memory. <i>IEEE Electron Device Letters</i> , 2015 , 36, 333-335	4.4	36
127	Transcriptomic profiling comparison of YAP over-expression and conditional knockout mouse tooth germs. <i>Genomics Data</i> , 2015 , 5, 228-30		2

126	Impact of program/erase operation on the performances of oxide-based resistive switching memory. <i>Nanoscale Research Letters</i> , 2015 , 10, 39	5	27
125	Investigation of LRS dependence on the retention of HRS in CBRAM. <i>Nanoscale Research Letters</i> , 2015 , 10, 61	5	23
124	Degradation of Gate Voltage Controlled Multilevel Storage in One Transistor One Resistor Electrochemical Metallization Cell. <i>IEEE Electron Device Letters</i> , 2015 , 36, 555-557	4.4	20
123	Improving resistance uniformity and endurance of resistive switching memory by accurately controlling the stress time of pulse program operation. <i>Applied Physics Letters</i> , 2015 , 106, 092103	3.4	30
122	Charge carrier hopping transport based on Marcus theory and variable-range hopping theory in organic semiconductors. <i>Journal of Applied Physics</i> , 2015 , 118, 045701	2.5	30
121	Improving the resistive switching reliability via controlling the resistance states of RRAM 2015 ,		1
120	Dynamic observation of oxygen vacancies in hafnia layer by in situ transmission electron microscopy. <i>Nano Research</i> , 2015 , 8, 3571-3579	10	27
119	A Physical Model for the Statistics of the Set Switching Time of Resistive RAM Measured With the Width-Adjusting Pulse Operation Method. <i>IEEE Electron Device Letters</i> , 2015 , 36, 1303-1306	4.4	11
118	Multiple heteroatom induced carrier engineering and hierarchical nanostructures for high thermoelectric performance of polycrystalline In ₄ Se _{2.5} . <i>Journal of Materials Chemistry A</i> , 2015 , 3, 1251-1257	13	37
117	Polaron effect and energetic disorder dependence of Seebeck coefficient in organic transistors. <i>Organic Electronics</i> , 2015 , 16, 113-117	3.5	18
116	Universal carrier thermoelectric-transport model based on percolation theory in organic semiconductors. <i>Physical Review B</i> , 2015 , 91,	3.3	37
115	Atomic View of Filament Growth in Electrochemical Memristive Elements. <i>Scientific Reports</i> , 2015 , 5, 13311	4.9	65
114	Resistance-switching mechanism of SiO ₂ :Pt-based Mott memory. <i>Journal of Applied Physics</i> , 2015 , 118, 245701	2.5	2
113	Effect of TiC Nano-inclusions on Thermoelectric and Mechanical Performance of Polycrystalline In ₄ Se _{2.65} . <i>Journal of the American Ceramic Society</i> , 2015 , 98, 3813-3817	3.8	9
112	Carrier-transport-path-induced switching parameter fluctuation in oxide-based resistive switching memory. <i>Materials Research Express</i> , 2015 , 2, 046304	1.7	9
111	Distance-dependent plasmon-enhanced fluorescence of upconversion nanoparticles using polyelectrolyte multilayers as tunable spacers. <i>Scientific Reports</i> , 2015 , 5, 7779	4.9	144
110	Conductance Quantization in Resistive Random Access Memory. <i>Nanoscale Research Letters</i> , 2015 , 10, 420	5	65
109	Effect of Pulse and dc Formation on the Performance of One-Transistor and One-Resistor Resistance Random Access Memory Devices. <i>Chinese Physics Letters</i> , 2015 , 32, 028502	1.8	1

108	Evolution of conductive filament and its impact on reliability issues in oxide-electrolyte based resistive random access memory. <i>Scientific Reports</i> , 2015 , 5, 7764	4.9	99
107	Superior Retention of Low-Resistance State in Conductive Bridge Random Access Memory With Single Filament Formation. <i>IEEE Electron Device Letters</i> , 2015 , 36, 129-131	4.4	44
106	YAP regulates the expression of Hoxa1 and Hoxc13 in mouse and human oral and skin epithelial tissues. <i>Molecular and Cellular Biology</i> , 2015 , 35, 1449-61	4.8	27
105	Conduction mechanism of a TaO(x)-based selector and its application in crossbar memory arrays. <i>Nanoscale</i> , 2015 , 7, 4964-70	7.7	38
104	Three-state resistive switching in HfO ₂ -based RRAM. <i>Solid-State Electronics</i> , 2014 , 98, 38-44	1.7	8
103	Enhancement of the Thermoelectric Performance of Polycrystalline In ₄ Se _{2.5} by Copper Intercalation and Bromine Substitution. <i>Advanced Energy Materials</i> , 2014 , 4, 1300599	21.8	64
102	An overview of the switching parameter variation of RRAM. <i>Science Bulletin</i> , 2014 , 59, 5324-5337		13
101	Multi-scale quantum point contact model for filamentary conduction in resistive random access memories devices. <i>Journal of Applied Physics</i> , 2014 , 115, 244507	2.5	45
100	Synthesis of upconversion NaYF ₄ :Yb ³⁺ ,Er ³⁺ particles with enhanced luminescent intensity through control of morphology and phase. <i>Journal of Materials Chemistry C</i> , 2014 , 2, 3671-3676	7.1	54
99	Direct Observation of Conversion Between Threshold Switching and Memory Switching Induced by Conductive Filament Morphology. <i>Advanced Functional Materials</i> , 2014 , 24, 5679-5686	15.6	218
98	Investigating the impact and reaction pathway of toluene on a SOFC running on syngas. <i>International Journal of Hydrogen Energy</i> , 2014 , 39, 12083-12091	6.7	25
97	Physical model of dynamic Joule heating effect for reset process in conductive-bridge random access memory. <i>Journal of Computational Electronics</i> , 2014 , 13, 432-438	1.8	35
96	Thermoelectric Seebeck effect in oxide-based resistive switching memory. <i>Nature Communications</i> , 2014 , 5, 4598	17.4	75
95	Limitation of the concept of transport energy in disordered organic semiconductors. <i>Europhysics Letters</i> , 2014 , 106, 17005	1.6	11
94	The fate of tars under solid oxide fuel cell conditions: A review. <i>Applied Thermal Engineering</i> , 2014 , 70, 687-693	5.8	26
93	High-Efficiency Energy Systems with Biomass Gasifiers and Solid Oxide Fuel Cells 2014 , 503-524		
92	Low temperature atomic layer deposited HfO ₂ film for high performance charge trapping flash memory application. <i>Semiconductor Science and Technology</i> , 2014 , 29, 045019	1.8	7
91	Operation methods of resistive random access memory. <i>Science China Technological Sciences</i> , 2014 , 57, 2295-2304	3.5	9

90	Set statistics in conductive bridge random access memory device with Cu/HfO ₂ /Pt structure. <i>Applied Physics Letters</i> , 2014 , 105, 193501	3.4	39
89	Resistive switching characteristics of Ti/ZrO ₂ /Pt RRAM device. <i>Chinese Physics B</i> , 2014 , 23, 117305	1.2	10
88	Simulation study of conductive filament growth dynamics in oxide-electrolyte-based ReRAM. <i>Journal of Semiconductors</i> , 2014 , 35, 104007	2.3	10
87	Gate induced resistive switching in 1T1R structure with improved uniformity and better data retention 2014 ,		7
86	Uniformity Improvement in 1T1R RRAM With Gate Voltage Ramp Programming. <i>IEEE Electron Device Letters</i> , 2014 , 35, 1224-1226	4.4	54
85	General Einstein relation model in disordered organic semiconductors under quasiequilibrium. <i>Physical Review B</i> , 2014 , 90,	3.3	49
84	Multilevel unipolar resistive switching with negative differential resistance effect in Ag/SiO ₂ /Pt device. <i>Journal of Applied Physics</i> , 2014 , 116, 154509	2.5	34
83	A unified physical model of Seebeck coefficient in amorphous oxide semiconductor thin-film transistors. <i>Journal of Applied Physics</i> , 2014 , 116, 104502	2.5	12
82	Statistical characteristics of reset switching in Cu/HfO ₂ /Pt resistive switching memory. <i>Nanoscale Research Letters</i> , 2014 , 9, 2500	5	13
81	Bipolar one diode-one resistor integration for high-density resistive memory applications. <i>Nanoscale</i> , 2013 , 5, 4785-9	7.7	45
80	Investigation on the RESET switching mechanism of bipolar Cu/HfO ₂ /Pt RRAM devices with a statistical methodology. <i>Journal Physics D: Applied Physics</i> , 2013 , 46, 245107	3	23
79	An experimental study of the interaction between tar and SOFCs with Ni/GDC anodes. <i>Applied Energy</i> , 2013 , 108, 149-157	10.7	47
78	Anode recirculation behavior of a solid oxide fuel cell system: A safety analysis and a performance optimization. <i>International Journal of Hydrogen Energy</i> , 2013 , 38, 2868-2883	6.7	38
77	In situ observation of nickel as an oxidizable electrode material for the solid-electrolyte-based resistive random access memory. <i>Applied Physics Letters</i> , 2013 , 102, 053502	3.4	54
76	Atomic-level quantized reaction of HfO _x memristor. <i>Applied Physics Letters</i> , 2013 , 102, 172903	3.4	88
75	Overcoming the Dilemma Between RESET Current and Data Retention of RRAM by Lateral Dissolution of Conducting Filament. <i>IEEE Electron Device Letters</i> , 2013 , 34, 873-875	4.4	26
74	Voltage and power-controlled regimes in the progressive unipolar RESET transition of HfO ₂ -based RRAM. <i>Scientific Reports</i> , 2013 , 3, 2929	4.9	118
73	Threshold Switching and Conductance Quantization in Al/HfO ₂ /Si(p) Structures. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 04CD06	1.4	12

72	Cycle-to-Cycle Intrinsic RESET Statistics in HfO_2 -Based Unipolar RRAM Devices. <i>IEEE Electron Device Letters</i> , 2013 , 34, 623-625	4.4	88
71	A Model for the Set Statistics of RRAM Inspired in the Percolation Model of Oxide Breakdown. <i>IEEE Electron Device Letters</i> , 2013 , 34, 999-1001	4.4	111
70	Quantum-size effects in hafnium-oxide resistive switching. <i>Applied Physics Letters</i> , 2013 , 102, 183505	3.4	139
69	Effect of dipole layer on the density-of-states and charge transport in organic thin film transistors. <i>Applied Physics Letters</i> , 2013 , 103, 253303	3.4	17
68	Effects of interaction between defects on the uniformity of doping HfO_2 -based RRAM: a first principle study. <i>Journal of Semiconductors</i> , 2013 , 34, 032001	2.3	20
67	Response to "comment on real-time observation on dynamic growth/dissolution of conductive filaments in oxide-electrolyte-based ReRAM". <i>Advanced Materials</i> , 2013 , 25, 165-7	24	13
66	Real-time observation on dynamic growth/dissolution of conductive filaments in oxide-electrolyte-based ReRAM. <i>Advanced Materials</i> , 2012 , 24, 1844-9	24	443
65	. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1556-1558	4.4	20
64	Recent advances in synthesis and surface modification of lanthanide-doped upconversion nanoparticles for biomedical applications. <i>Biotechnology Advances</i> , 2012 , 30, 1551-61	17.8	260
63	Nitrogen-induced improvement of resistive switching uniformity in a HfO_2 -based RRAM device. <i>Semiconductor Science and Technology</i> , 2012 , 27, 125008	1.8	50
62	Effect of low constant current stress treatment on the performance of the $\text{Cu/ZrO}_2/\text{Pt}$ resistive switching device. <i>Semiconductor Science and Technology</i> , 2012 , 27, 105007	1.8	11
61	Effect of bandgap engineering on the performance and reliability of a high-k-based nanoscale charge trap flash memory. <i>Journal Physics D: Applied Physics</i> , 2012 , 45, 065104	3	3
60	Improving the electrical performance of resistive switching memory using doping technology. <i>Science Bulletin</i> , 2012 , 57, 1235-1240		22
59	Improved performance of non-volatile memory with $\text{Au-Al}_2\text{O}_3$ core-shell nanocrystals embedded in HfO_2 matrix. <i>Applied Physics Letters</i> , 2012 , 100, 203509	3.4	13
58	Improved current distribution in resistive memory on flexible substrate using nitrogen-rich TaN electrode. <i>Applied Physics Letters</i> , 2012 , 101, 243507	3.4	11
57	Analysis and modeling of resistive switching statistics. <i>Journal of Applied Physics</i> , 2012 , 111, 074508	2.5	83
56	Low-cost 13.56MHz Rectifier Based on Organic Diode. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1402, 13		1
55	Square optical vortices generated by binary spiral zone plates. <i>Applied Physics Letters</i> , 2011 , 98, 151106	3.4	35

54	Improvement of resistive switching characteristics in ZrO ₂ film by embedding a thin TiO _x layer. <i>Nanotechnology</i> , 2011 , 22, 254028	3.4	43
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